

TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N CHANNEL IGBT

GT20J301

HIGH POWER SWITCHING APPLICATIONS

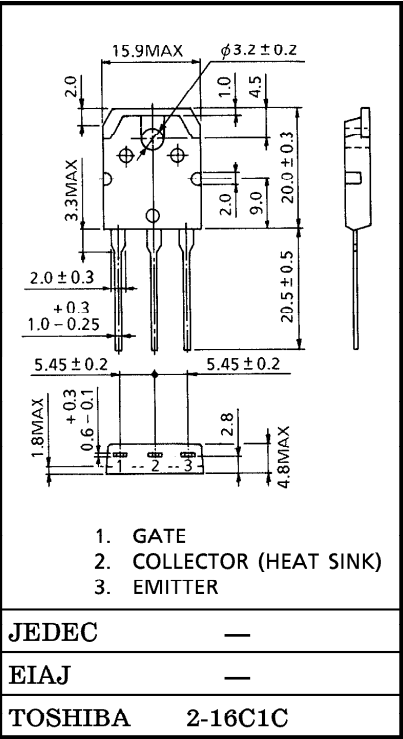
MOTOR CONTROL APPLICATIONS

- The 3rd Generation
- Enhancement-Mode
- High Speed : $t_f=0.30\mu s$ (Max.)
- Low Saturation Voltage : $V_{CE(sat)}=2.7V$ (Max.)
- FRD included between Emitter and Collector

MAXIMUM RATINGS (Ta = 25°C)

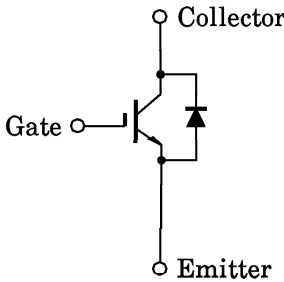
CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		V_{CES}	600	V
Gate-Emitter Voltage		V_{GES}	± 20	V
Collector Current	DC	I_C	20	A
	1ms	I_{CP}	40	A
Emitter-Collector Forward Current	DC	I_F	20	A
	1ms	I_{FM}	40	A
Collector Power Dissipation (Tc=25°C)		P_C	130	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C

Unit in mm



Weight : 4.6g

EQUIVALENT CIRCUIT



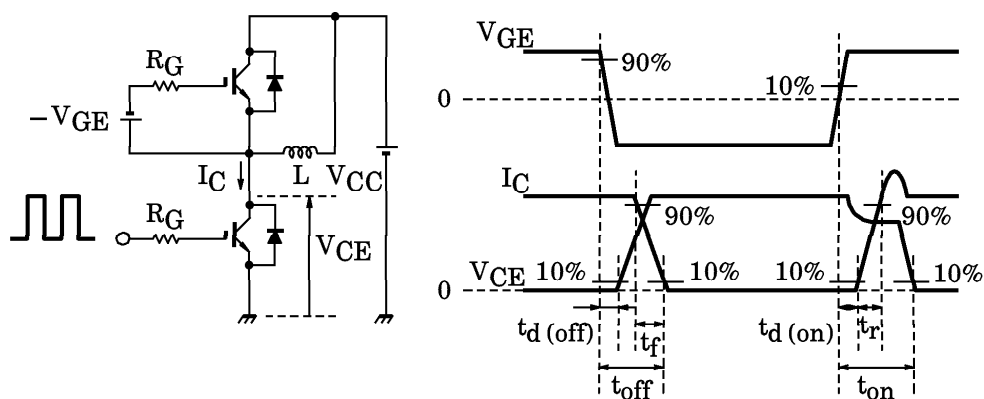
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ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GES}	$V_{GE} = \pm 20\text{V}$, $V_{CE} = 0$	—	—	± 500	nA
Collector Cut-Off Current		I_{CES}	$V_{CE} = 600\text{V}$, $V_{GE} = 0$	—	—	1.0	mA
Gate-Emitter Cut-Off Voltage		$V_{GE}(\text{OFF})$	$I_C = 2\text{mA}$, $V_{CE} = 5\text{V}$	5.0	—	8.0	V
Collector-Emitter Saturation Voltage		$V_{CE}(\text{sat})$	$I_C = 20\text{A}$, $V_{GE} = 15\text{V}$	—	2.1	2.7	V
Input Capacitance		C_{ies}	$V_{CE} = 20\text{V}$, $V_{GE} = 0$, $f = 1\text{MHz}$	—	1450	—	pF
Switching Time	Rise Time	t_r	Inductive Load $V_{CC} = 300\text{V}$, $I_C = 20\text{A}$ $V_{GG} = \pm 15\text{V}$, $R_G = 56\Omega$ (Note)	—	0.12	—	μs
	Turn-On Time	t_{on}		—	0.40	—	
	Fall Time	t_f		—	0.15	0.30	
	Turn-Off Time	t_{off}		—	0.70	—	
Peak Forward Voltage		V_F	$I_F = 20\text{A}$, $V_{GE} = 0$	—	—	2.0	V
Reverse Recovery Time		t_{rr}	$I_F = 20\text{A}$, $di/dt = -100\text{A}/\mu\text{s}$	—	—	200	ns
Thermal Resistance (IGBT)		$R_{th(j-c)}$	—	—	—	0.96	$^\circ\text{C}/\text{W}$
Thermal Resistance (Diode)		$R_{th(j-e)}$	—	—	—	2.5	$^\circ\text{C}/\text{W}$

(Note) Switching time measurement circuit and input/output waveforms



Switching loss measurement waveforms

